

n-channel JFET 8 switch array

Designed for Military and Industrial Applications . . .

■ High Speed Sense/Drive Switch Array

ABSOLUTE MAXIMUM RATINGS (25°C)

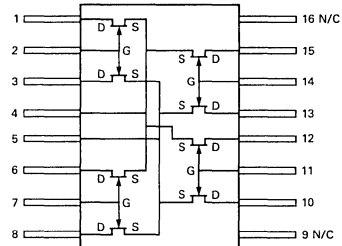
For Each Individual Chip:

Gate-Source Voltage	– 25V
Gate-Drain Voltage	– 25V
Gate Current	100 mA
Drain Current	400 mA
Storage Temp Range	– 65°C to + 200°C
Oper Temp Range	– 55°C to + 150°C
Lead Temp (Soldering, 10 sec)	+ 300°C
Power Dissipation	300 mW
Derate above 25°C	2.3 mW/°C

BENEFITS

- Low $R_{DS(ON)} < 7 \text{ OHMS}$
- High Speed
- $T_R = 1 \text{ ns}$; $T_{(OFF)} = 5 \text{ ns}$
- High Radiation Resistance

PACKAGE: 16 PIN FLAT PACKAGE



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic		Min	Typical	Max	Unit	Test Condition
1	S T A T I C	I_{GSSR}		2.0	nA	$V_{GS} = -15V, V_{DS} = 0$
2		I_{GSSR}		5	μA	$V_{GS} = -15V, V_{DS} = 0, T_A = 125^\circ C$
3		BV_{GSS}	– 25		V	$I_G = 8\mu A, V_{DS} = 0$
4		$V_{GS(off)}$	– 5	– 10	V	$V_{DS} = 5V, I_D = 100 \text{ nA}$
5		$I_{D(off)}$		1	nA	$V_{DS} = 5V, V_{GS} = -10V$
6		$I_{D(off)}$		5	μA	$V_{DS} = 5V, V_{GS} = -10V, T_A = 125^\circ C$
7		$R_{DS(on)}$		7	ohm	$V_{GS} = 0, I_D = 10 \text{ mA}$
8	D Y N A M I C	C_{iss}		30	pf	$V_{DS} = 0, V_{GS} = -10V, f = 1 \text{ MHz}$
9		C_{rss}		15	pf	$v_{DS} = 0, V_{GS} = -10V, f = 1 \text{ MHz}$
10		t_d	3		ns	$V_{DD} = 1.5V, V_{GS(on)} = 0, V_{GS(off)} = 12V$
11		$t_{(off)}$	5		ns	
12		t_f	5		ns	
13		t_r	1		ns	